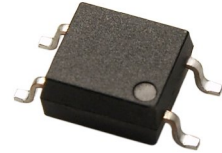


Features:

- Halogens free
- AC input response
- Current transfer ratio
(CTR: Min. 20% at $I_F = \pm 1\text{mA}$, $V_{CE} = 5\text{V}$)
- High isolation voltage between input and output (Viso=3750 V rms)
- Compact small outline package
- Pb free and RoHS compliant.
- UL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved
- CSA approved (No. 1408633)

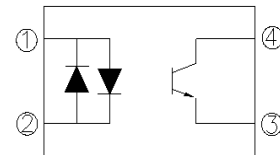


Description

The EL354N-G series of devices each consist of two infrared emitting diode, connected in inverse parallel, optically coupled to a phototransistor detector.

They are packaged in a 4-pin small outline package.

Schematic



Pin Configuration

1. Anode / Cathode
2. Cathode / Anode
3. Emitter
4. Collector

Applications

- AC line monitor
- Programmable controllers
- Telephone line interface
- Unknown polarity DC sensor

Absolute Maximum Ratings (T_a=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward current	I _F	±50	mA
	Peak forward current (t = 10μs)	I _{FM}	1	A
	Power dissipation	P _D	70	mW
	No derating required up to T _a = 100°C			
Output	Power dissipation	P _C	150	mW
	Derating factor (above T _a = 80°C)		3.7	mW/°C
	Collector-Emitter voltage	V _{CEO}	80	V
	Emitter-Collector voltage	V _{ECO}	6	V
Total power dissipation		P _{tot}	200	mW
Isolation voltage ^{*1}		V _{iso}	3750	V rms
Operating temperature		T _{opr}	-55~+100	°C
Storage temperature		T _{stg}	-55~+125	°C
Soldering temperature ^{*2}		T _{sol}	260	°C

Notes

*1 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1 & 2 are shorted together, and pins 3 & 4 are shorted together.

*2 For 10 seconds.

Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Forward voltage	V_F	-	1.2	1.4	V	$I_F = \pm 20\text{mA}$
Reverse current	I_R	-	-	10	μA	$V_R = 4\text{V}$
Input capacitance	C_{in}	-	50	250	pF	$V = 0, f = 1\text{KHz}$

Output

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Collector-Emitter dark current	I_{CEO}	-	-	100	nA	$V_{CE} = 20\text{V}, I_F = 0\text{mA}$
Collector-Emitter breakdown voltage	BV_{CEO}	80	-	-	V	$I_C = 0.1\text{mA}$
Emitter-Collector breakdown voltage	BV_{ECO}	6	-	-	V	$I_E = 0.01\text{mA}$

Transfer Characteristics ($T_a=25^{\circ}\text{C}$ unless specified otherwise)

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Current Transfer ratio	EL354	20	-	300	%	$I_F = \pm 1\text{mA}, V_{CE} = 5\text{V}$
	EL354A	50	-	150		
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	0.1	0.2	V	$I_F = \pm 20\text{mA}, I_C = 1\text{mA}$
Isolation resistance	R_{IO}	5×10^{10}	10^{11}	-	Ω	$V_{IO} = 500\text{Vdc}, 40\sim 60\% \text{R.H}$
Cut-off frequency	f_c	-	80	-	kHz	$V_{CE} = 5\text{V}, I_C = 2\text{mA}, R_L = 100\Omega, -3\text{dB}$
Floating capacitance	C_{IO}	-	0.6	1.0	pF	$V_{IO} = 0, f = 1\text{MHz}$
Rise time	T_r	-	6	18	μs	$V_{CE} = 2\text{V}, I_C = 2\text{mA}, R_L = 100\Omega$
Fall time	T_f	-	8	18	μs	

* Typical values at $T_a = 25^{\circ}\text{C}$

Typical Performance Curves

Figure 1. Forward Current vs Forward Voltage

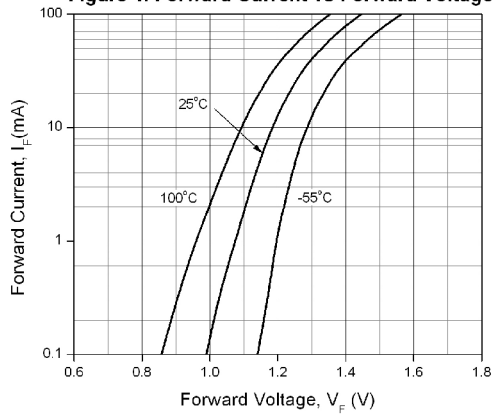


Figure 2. Normalized Collector Current vs Forward Current

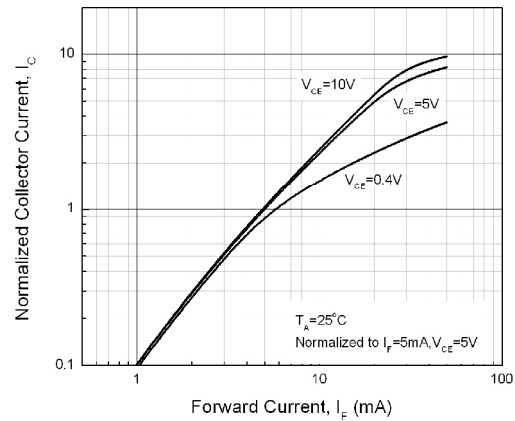


Figure 3. Normalized Current Transfer Ratio vs Forward Current

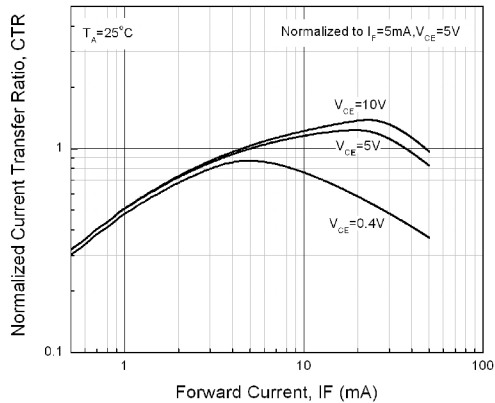


Figure 4. Normalized Collector Current vs Ambient Temperature

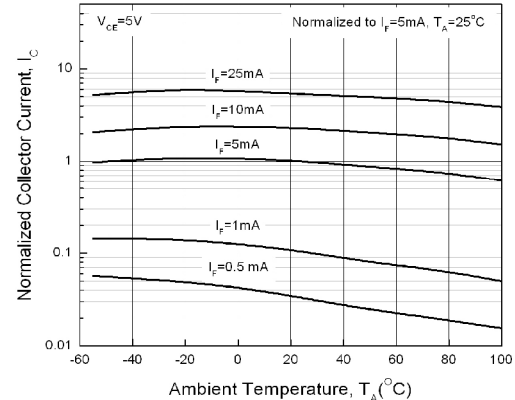


Figure 5. Collector Current vs Collector-Emitter Voltage

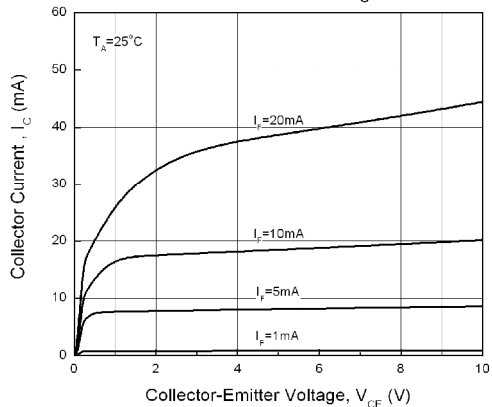


Figure 6. Collector Current vs Collector-Emitter Voltage

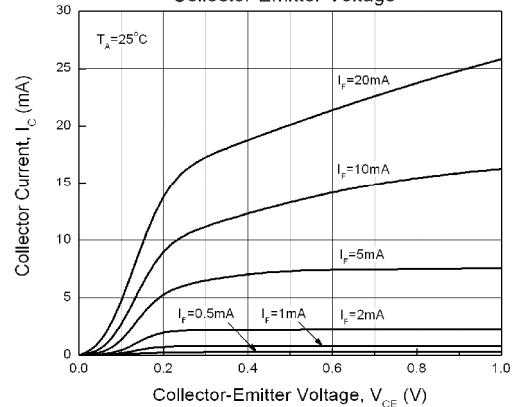


Figure 7. Collector Dark Current vs Ambient Temperature

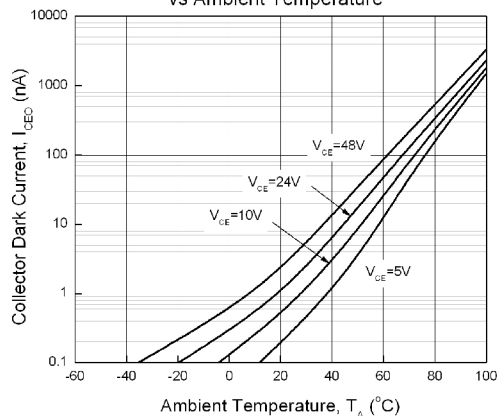


Figure 8. Switching Time vs Load Resistance

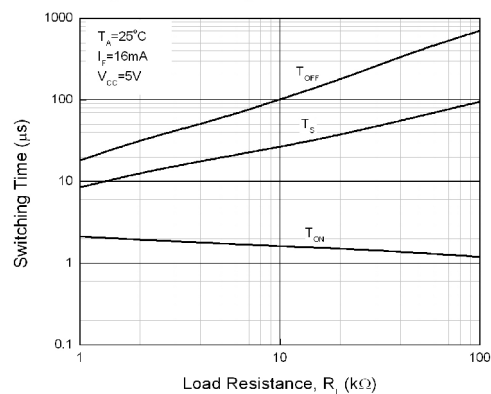


Figure 9. Collector-Emitter Saturation Voltage vs Ambient Temperature

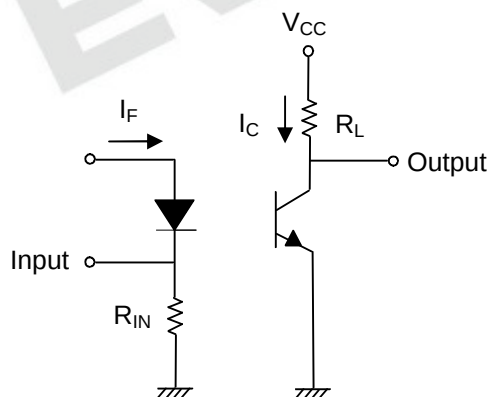
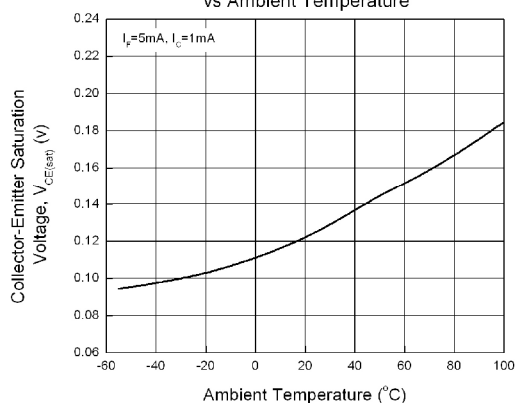


Figure 10. Switching Time Test Circuit & Waveforms

Order Information

Part Number

EL354N(X)(Y)-VG

Note

354N = Part No.

X = CTR Rank option (A, or none)

Y = Tape and reel option (TA, TB, or none).

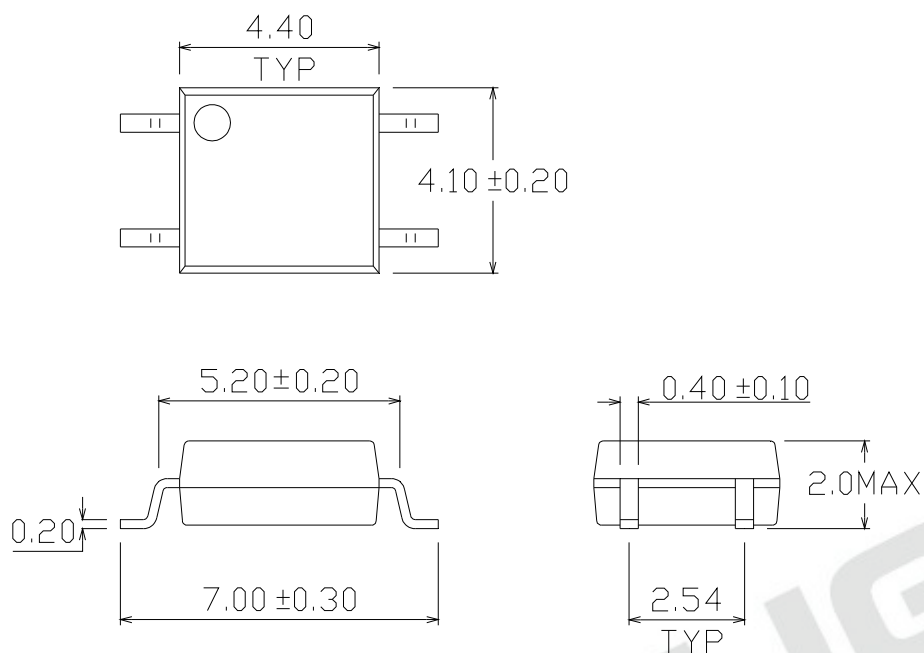
V = VDE (option)

G = Halogens free

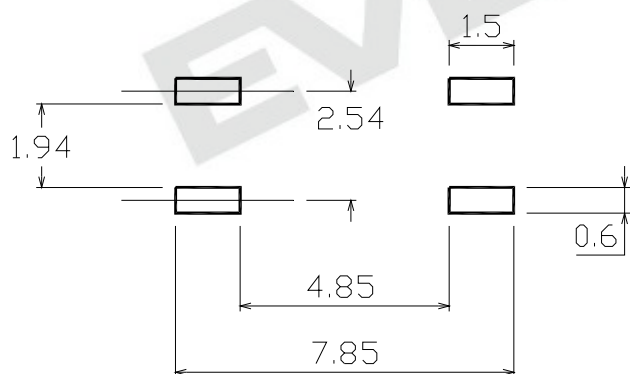
Option	Description	Packing quantity
None	Standard SMD option	100 units per tube
-V	Standard SMD option + VDE	100 units per tube
(TA)	TA Tape & reel option	3000 units per reel
(TB)	TB Tape & reel option	3000 units per reel
(TA)-V	TA Tape & reel option + VDE	3000 units per reel
(TB)-V	TB Tape & reel option + VDE	3000 units per reel

Package Drawings

(Dimensions in mm)



Recommended pad layout for surface mount leadform



Device Marking

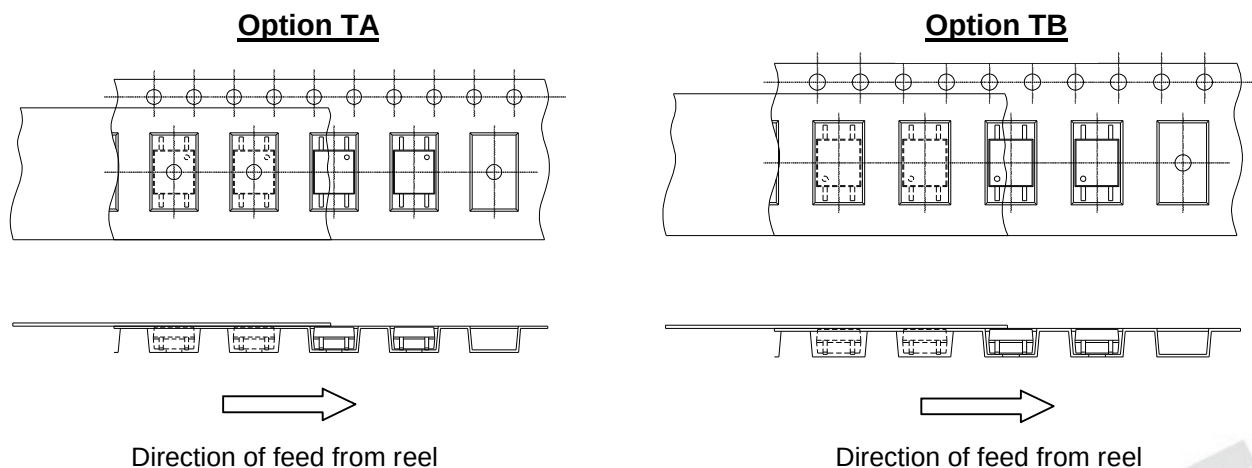


Notes

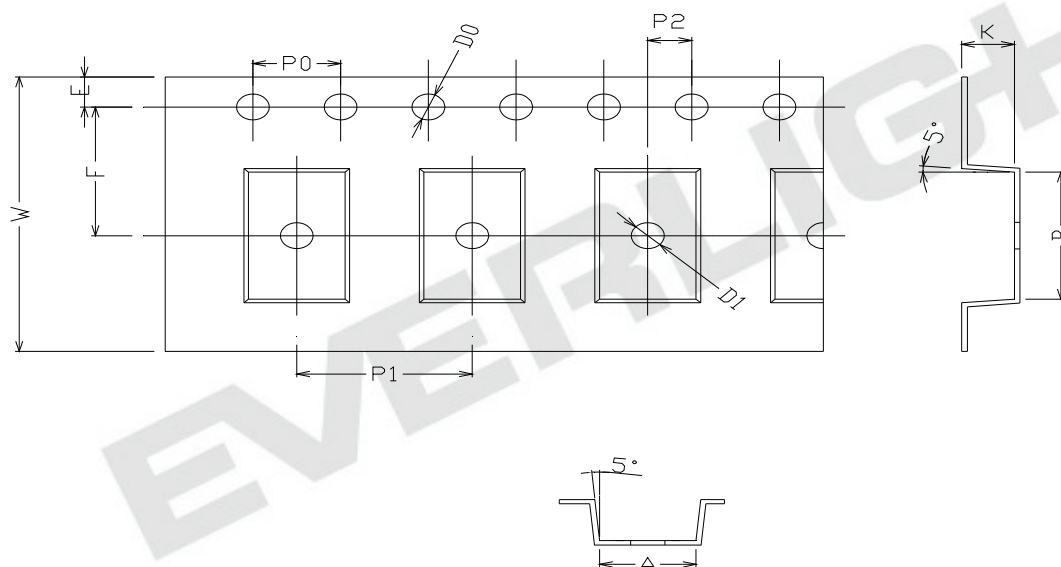
EL	denotes Everlight
354N	denotes Device Number
R	denotes CTR Rank (A or none)
Y	denotes 1 digit Year code
WW	denotes 2 digit Week code
V	denotes VDE approved (optional)

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Tape & Reel Packing Specifications



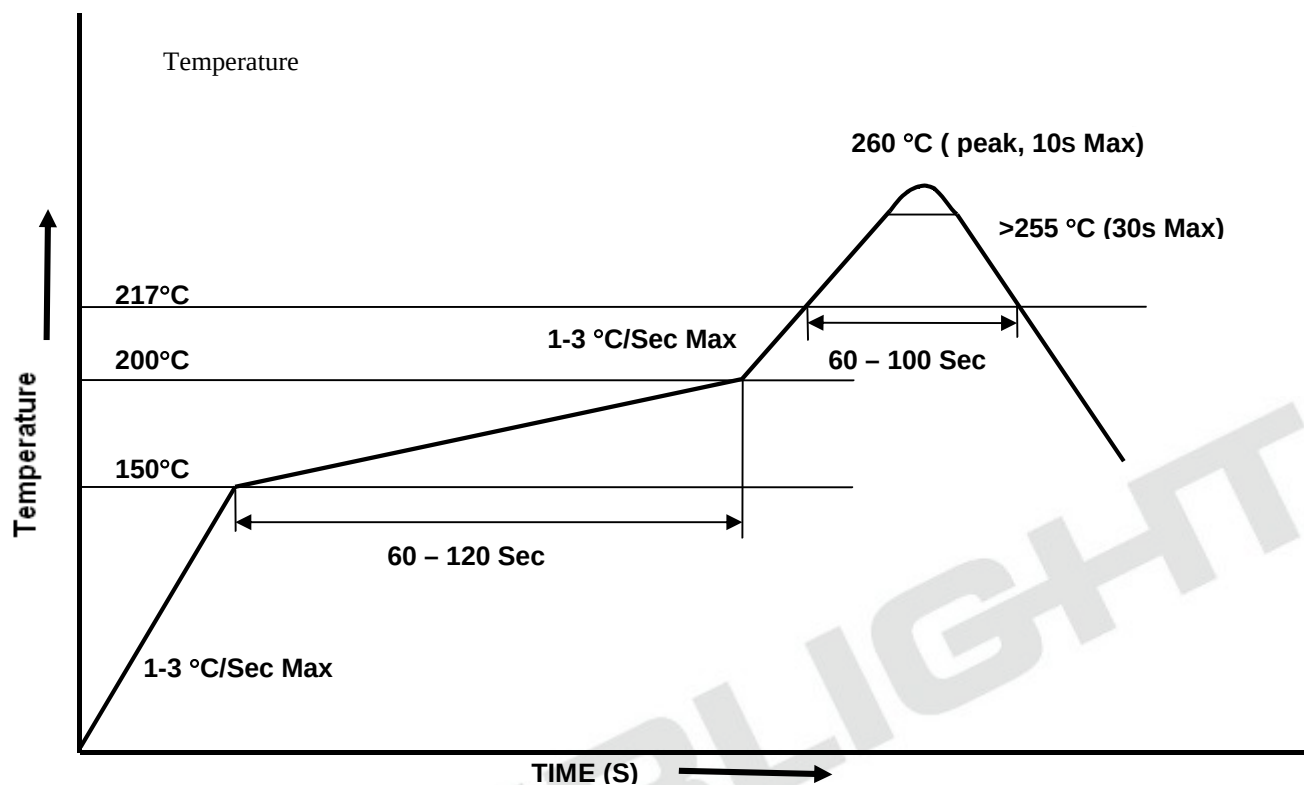
Tape dimensions



Dimension No.	A	B	Do	D1	E	F
Dimension (mm)	4.4 ± 0.1	7.4 ± 0.1	$1.5 + 0.1/-0$	1.5 ± 0.1	1.75 ± 0.1	7.5 ± 0.1

Dimension No.	Po	P1	P2	t	W	K
Dimension (mm)	4.0 ± 0.15	8.0 ± 0.1	2.0 ± 0.1	0.25 ± 0.03	16.0 ± 0.2	2.4 ± 0.1

Solder Reflow Temperature Profile



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